

<b>INFORMATION DISCLOSURE CITATION FORM FOR PATENT APPLICATION (FORM PTO-1449) (Substitute)</b>			Docket No.: YOR920030207US1  Applicant(s): Hyungjun KIM et al.  Filing Date:		Serial No.:   Group:	
<b>U.S. PATENTS</b>						
Initials	Patent Number	Issue Date	Name	Class	Sub-class	Filing date
	2003/0201537A  U.S. Patent Application Serial No. 10/699,226	10/30/03	Lane et al.  KIM et al.			
<b>FOREIGN PATENT DOCUMENTS</b>						
Initials	Document Number	Date	Country	Name	Translation? Yes/No/n/a	
<b>OTHER DOCUMENTS (Title, Author, Date, Pages, Etc., if known)</b>						
	Rossnagel et al., Plasma-enhanced atomic layer deposition of Ta and Ti for inter- connect diffusion barriers, J. Vac. Sci. Technol. B 18(4), July/Aug 2002					
	KIM et. al., Growth of cubic-TaN thin films..J.App.Physics, Vol. 92, No.12,2002					
	Kim et al., Growth kinetics and initial stage growth during plasma-enhanced Ti atomic layer deposition, J. Vac. Sci. Technol. A 20(3), May/June 2002					
	Kim et al., Diffusion barrier properties of transition metal thin films grown by plasma-enhanced atomic layer deposition, J. Vac. Sci. Technol. B 20(4), J/A 2002					
Examiner's Signature:				Date Considered:		
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